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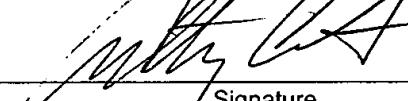
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope, with sufficient postage, addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

October 7, 2003

Date of Deposit

Anthony P. Curtis, Ph.D., Reg. No. 46,193

Name of Applicant, Assignee or  
Registered Representative



Signature

10/7/03

Date of Signature

Our Case No.: 10322/57  
Client Ref. No. TF03009

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Kuang-Chien Hsieh et al.

Serial No.: Not yet assigned

Filing Date: Herewith

For: ADHESIVE BONDING WITH LOW  
TEMPERATURE GROWN  
AMORPHOUS OR  
POLYCRYSTALLINE COMPOUND  
SEMICONDUCTORS

Examiner: Not yet assigned

Group Art Unit No.: Not yet assigned

### INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed below and on the attached Form PTO-1449 be considered by the Examiner and

FORM PTO-1449	SERIAL NO. Not yet assigned	CASE NO. 10322/57 Client Ref. No. TF03009
<b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (use several sheets if necessary)	FILING DATE Herewith	GROUP ART UNIT Not yet assigned
	APPLICANT(S): Kuang-Chien Hsieh et al.	

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	A3	K. L. Chang, G.W. Pickrell, D.E. Wohlert, J.H. Epple, H.C. Lin, K.Y. Cheng and K.C. Hsieh, <i>Microstructure and Wet Oxidation of Low-Temperature-Grown Amorphous (Al/Ga,As)</i> , American Institute of Physics, Vol. 89 No. 1, pgs. 747-752, January 1, 2001.
	A4	J.J. Epple, K.L. Chang, C.F. Xu, G.W. Pickrell, K.Y. Chang, and K.C. Hsieh, <i>Formation of Highly Conductive Polycrystalline GaAs from Annealed Amorphous (Ga,As)</i> , American Institute of Physics, pgs. 5331-5336, May 1, 2003.
	A5	H.C. Lin, W.H. Wang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of 1.55μm VCSELs on Si Using Metallic Bonding</i> , Electronics Letters, Vol. 38 No. 11, May 23, 2002.
	A6	H.C. Lin, K.L. Chang, K.C. Hsieh, K.Y. Cheng, <i>Metallic Wafer Bonding for the Fabrication of Long-Wavelength Vertical-Cavity Surface-Emitting Lasers</i> , Journal of Applied Physics, Vol. 92 No. 7, pgs. 4132-4134, October 1, 2002.
	A7	H.C. Lin, K.L. Chang, G.W. Pickrell, K.C. Hsieh and K.Y. Cheng, <i>Low Temperature Wafer Bonding by Spin on Glass</i> , Journal of Vacuum Science & Technology B, Vol. 20 No. 2, pgs. 752-754, March/April 2002.
	A8	G.W. Pickrell, K.L. Chang, J.H. Epple, K.Y. Chang and K.C. Hsieh, <i>Protection of In<sub>0.25</sub>Ga<sub>0.75</sub>As/GaAs Structures During Lateral Oxidation Using an Amorphous InGaP Layer</i> , American Vacuum Society, Vol. 20 No. 3, pgs. 876-879, May/June 2002.
	A9	G.W. Pickrell, K.L. Chang, H.C. Lin, K.C. Hsieh and K.Y. Cheng, <i>Very-Low-Temperature Molecular Beam Epitaxial Growth of GaP/AlAs Heterostructures for Distributed Bragg Reflector Applications</i> , American Vacuum Society, pgs. 1536-1540, July/Aug. 2001.
	A10	G.W. Pickrell, H.C. Lin, K.L. Chang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of GaP/Al-Oxide Distributed Bragg Reflectors for the Visible Spectrum</i> , Applied Physics Letters, Vol. 78 No. 8, pgs. 1044-1046, February 19, 2001.
	A11	Frank Shi, Scott McLaren, Chaofeng Xu, K.Y. Cheng and K.C. Hsieh, <i>Hybrid-integrated GaAs/GaAs and InP/GaAs Semiconductors Through Wafer Bonding Technology: Interface Adhesion and Mechanical Strength</i> : American Institute of Physics, pgs. 5750-5756, May 1, 2003.
	A12	Frank F. Shi, Kuo-Lih Chang and Veronica I. Lai, <i>UltraWafer, Inc., A UIUC Semiconductor Start-up, Speeding Up What's Next</i> , pgs. 2-24,
	A13	D.E. Wohlert, H.C. Lin, K.L. Chang, G.W. Pickrell, Jr., J.H. Epple, K.C. Hsieh, K.Y. Cheng, <i>Fabrication of a Substrate-Independent Aluminum Oxide-GaAs Distributed Bragg Reflector</i> , Applied Physics Letters, Vol. 75 No. 10, pgs. 1371-1373, September 6, 1999.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

made of record. Copies of the listed documents required by 37 C.F.R. § 1.98(a)(2) are enclosed for the convenience of the Examiner.

The references now cited are the following:

OTHER ART – NON PATENT LITERATURE DOCUMENTS
L.J. Chou, K.C. Hsieh, D.E. Wohlert and K.Y. Cheng, <i>Formation of Amorphous Aluminum Oxide and Gallium Oxide on InP Substrates by Water Vapor Oxidation</i> , American Institute of Physics, pgs. 6932-6934, December 15, 1998.
L.J. Chou, K.C. Hsieh, A. Moy, D.E. Wohlert, G. Pickrell and K.Y. Cheng, <i>Improving the Al-Bearing Native-Oxide/GaAs Interface Formed by Wet Oxidation with a Thin GaP Barrier Layer</i> , American Institute of Physics, pgs. 2722-2724, May 25, 2003.
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### REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS	
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In accordance with 37 C.F.R. § 1.97(g),(h), this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed to be an admission that the information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b).

This Information Disclosure Statement is being filed prior to the receipt of the first Official Action reflecting an examination on the merits and hence is believed to be timely filed in accordance with 37 C.F.R. § 1.97(b). No fees are believed to be due in connection with filing of this Information Disclosure Statement, however, should any fees under 37 C.F.R. §§ 1.16 to 1.21 be deemed necessary for any reason relating to these material, the Commissioner is hereby authorized to deduct said fees from Brinks Hofer Gilson & Lione Deposit Account No. 23-1925. A duplicate copy of this document is enclosed.

Applicant(s) respectfully request that the listed documents be made of record in the present case.

Respectfully submitted,



Anthony P. Curtis, Ph.D.  
Registration No. 46,193  
Agent for Applicant(s)

BRINKS HOFER GILSON & LIONE  
P.O. Box 10395  
Chicago, IL 60610  
(312) 321-4200

**CERTIFICATE OF MAILING**

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October 7, 2003

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Chicago, IL 60610  
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